

## 2SC4410G

## Silicon NPN epitaxial planar type

## For UHF amplification

#### ■ Features

- Allowing the small current and low voltage operation
- High transition frequency f<sub>T</sub>
- S-Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing

## ■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol	Symbol Rating		
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	10	V	
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	7	V	
Emitter-base voltage (Collector open)	$V_{EBO}$	2	V	
Collector current	$I_C$	10	mA	
Collector power dissipation	P <sub>C</sub>	50	mW	
Junction temperature	T <sub>j</sub>	150	°C	
Storage temperature	T <sub>stg</sub>	-55 to +150	°C	

### Package

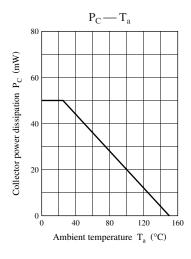
- Code
  - SMini3-F2
- Marking Symbol: 2X
- Pin Name
  - 1: Base
  - 2: Emitter
  - 3: Collector

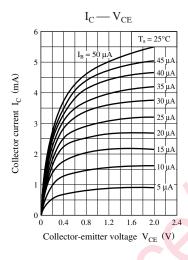
### ■ Electrical Characteristics $T_a = 25$ °C $\pm 3$ °C

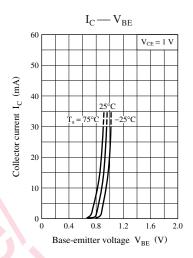
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{CB} = 10 \text{ V}, I_{E} = 0$			1	μΑ
Emitter-base cutoff current (Collector open)	$I_{EBO}$	$V_{EB} = 1.5 \text{ V}, I_{C} = 0$			1	μΑ
Forward current transfer ratio	$h_{FE}$	$V_{CE} = 1 \text{ V}, I_C = 1 \text{ mA}$	50		200	_
Transition frequency	$f_T$	$V_{CE} = 1 \text{ V}, I_{C} = 1 \text{ mA}, f = 0.8 \text{ GHz}$		4		GHz
Collector output capacitance (Common base, input open circuited)	C <sub>ob</sub>	$V_{CB} = 1 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		0.4		pF
Foward transfer gain	S <sub>21e</sub>   2	$V_{CE} = 1 \text{ V}, I_{C} = 1 \text{ mA}, f = 0.8 \text{ GHz}$		6.0		dB
Maximum unilateral power gain	$G_{UM}$	$V_{CE} = 1 \text{ V}, I_{C} = 1 \text{ mA}, f = 0.8 \text{ GHz}$		15		dB
Noise figure	NF	$V_{CE} = 1 \text{ V}, I_{C} = 1 \text{ mA}, f = 0.8 \text{ GHz}$		3.5		dB

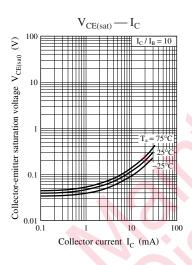
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

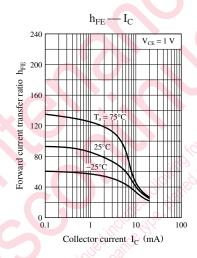
<sup>2.</sup> Handle the product with care because this is sensitive to the electrostatic breakdown by its structure

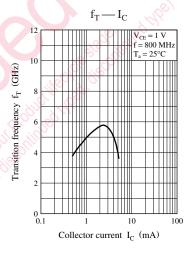


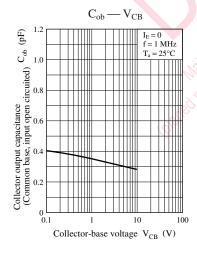


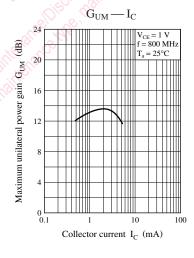


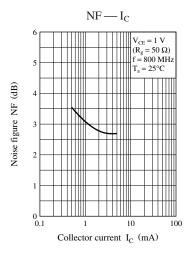






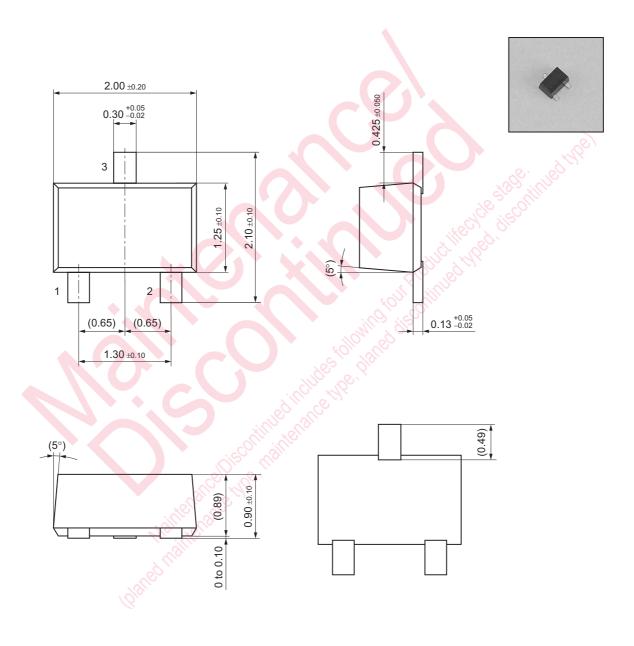






2 SJC00365AED

SMini3-F2 Unit: mm



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